# Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.42 \text{ V}$  at  $I_F = 5 \text{ A}$ 

#### **Features**

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- This is a Pb-Free Package

## **Typical Applications**

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

#### **Mechanical Characteristics**

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

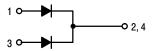


ON Semiconductor®

www.onsemi.com

VERY LOW FORWARD VOLT-AGE, LOW LEAKAGE SCHOT-TKY BARRIER RECTIFIERS 30 AMPERES, 80 VOLTS

#### **PIN CONNECTIONS**





TO-220FP CASE 221AH

#### **MARKING DIAGRAMS**



A = Assembly Location

Y = Year WW = Work Week AKA = Polarity Designator

#### **ORDERING INFORMATION**

= Pb-Free Package

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### **MAXIMUM RATINGS**

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	80	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 125$ °C)	Per device Per diode	I <sub>F(AV)</sub>	30 15	A
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 120°C)	Per device Per diode	I <sub>FRM</sub>	60 30	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I <sub>FSM</sub>	160	А
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T <sub>stg</sub>	-40 to +150	°C
Voltage Rate of Change (Rated V <sub>R</sub> )		dv/dt	10,000	V/µs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Rating		Symbol	Value	Unit
Maximum Thermal Resistance (insertion mounted to 1 oz FR4 Board)	Junction-to-Case	$R_{\theta JC}$	4.0	°C/W
(insertion mounted to 1 oz FR4 board)	Junction-to-Ambient	$R_{\theta JA}$	105	°C/W

<sup>1.</sup> Junction-to-Case, using large Heatsink attached to device.

#### **ELECTRICAL CHARACTERISTICS** (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 3)	V <sub>F</sub>			V
$(I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.47	_	
$(I_F = 7.5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.52	_	
$(I_F = 15 \text{ A}, T_J = 25^{\circ}\text{C})$		0.66	0.80	
$(I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$		0.42	_	
$(I_F = 7.5 \text{ A}, T_J = 125^{\circ}\text{C})$		0.48	_	
$(I_F = 15 \text{ A}, T_J = 125^{\circ}\text{C})$		0.60	0.65	
Maximum Instantaneous Reverse Current (Note 3)	I <sub>R</sub>			
(Rated dc Voltage, T <sub>J</sub> = 25°C)		15	200	μΑ
(Rated dc Voltage, T <sub>J</sub> = 125°C)		10	35	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **ORDERING INFORMATION**

Device	Package	Shipping
NTSJ30U80CTG	TO-220FP (Pb-Free)	50 Units / Rail

<sup>2.</sup> Junction-to-Ambient, using with no Heatsink.

<sup>3.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq 2.0\%$ 

#### **TYPICAL CHARACTERISITICS**

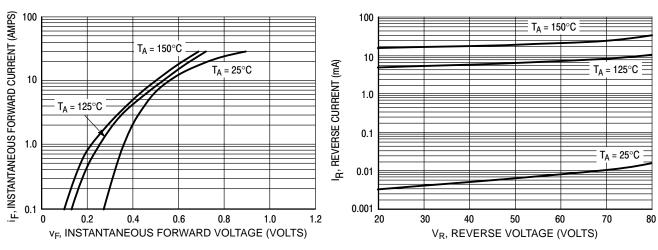
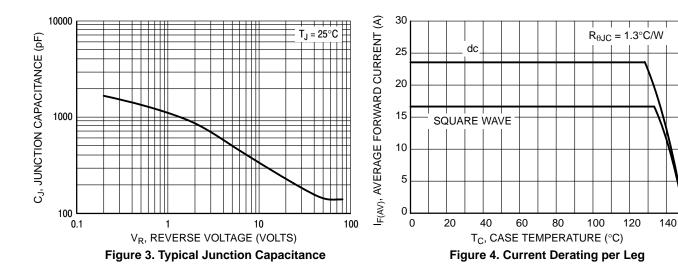
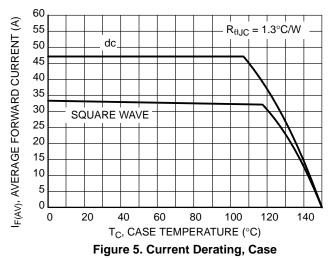


Figure 1. Typical Forward Voltage

**Figure 2. Typical Reverse Current** 





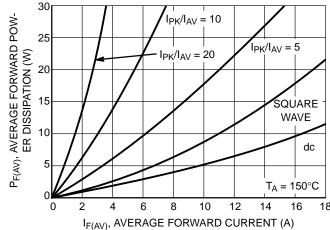


Figure 6. Forward Power Dissipation

## **TYPICAL CHARACTERISITICS**

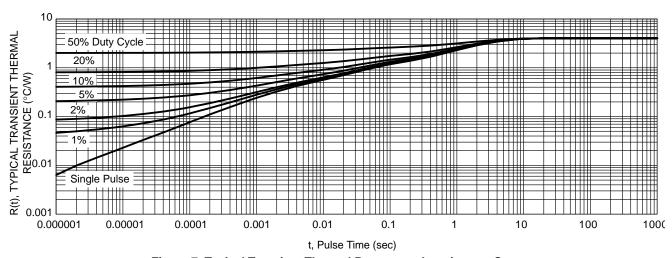
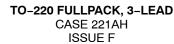
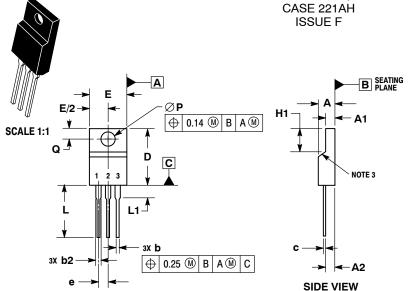
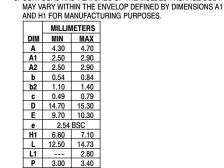


Figure 7. Typical Transient Thermal Response, Junction-to-Case



**DATE 30 SEP 2014** 

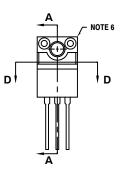


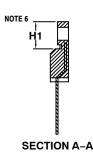


NOTES:

## SECTION D-D

**FRONT VIEW** 





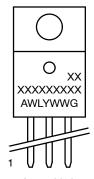
**ALTERNATE CONSTRUCTION** 

## **GENERIC MARKING DIAGRAM\***

 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR UNCONTROLLED IN THIS AREA.

3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
6. CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY.

MAY VARY WITHIN THE ENVEL OR DEFINED BY UNIENSIONS A1



= Assembly Location

WL = Wafer Lot

= Year

WW = Work Week

G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:		STYLE 2:	
PIN 1.	MAIN TERMINAL 1	PIN 1.	CATHODE
2.	MAIN TERMINAL 2	2.	ANODE
3.	GATE	3.	GATE

DOCUMENT NUMBER:	98AON52577E	Electronic versions are uncontrolled except when accessed directly from the Document Report Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION	TO-220 FULL PACK 3-1 FA	ΔD	PAGE 1 OF 1

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales